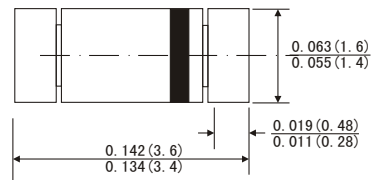


FEATURES

- Metal-on-silicon junction
- Low turn-on voltage
- Ultrafast switching speed
- Primarily intended for high level UHF detection and pulse applications with broad dynamic range
- The diode is also available in the DO-35 case with type designation BAT29.
- High temperature soldering guaranteed: 260°C / 10 seconds at terminals
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

MiniMELF



MECHANICAL DATA

- Case: MiniMELF glass case(SOD-80)
- Polarity: Color band denotes cathode end
- Weight: Approx. 0.05 gram

Dimensions in inches and (millimeters)

ABSOLUTE RATINGS(LIMITING VALUES)

	Symbols	Value	Units
Peak Reverse Voltage	V _{RRM}	5	V
Forward Continuous Current	I _F	30	mA
Surge non repetitive Forward current t _p <1s	I _{FSM}	2.0	A
Junction and Storage temperature range	T _{STG}	-55 to+150	°C
Junction temperature	T _J	125	°C

ELECTRICAL CHARACTERISTICS

	Symbols	Min.	Typ.	Max.	Units
Reverse breakover voltage at I _R =100μA	V _R	5			V
Leakage current at V _R =1V	I _R			50	nA
Forward voltage drop at I _F =10mA Test pulse:t _p < 300μs δ < 2%	V _F			0.55	V
Junction Capacitance at V _R =0V ,f=1GHz	C _J			1.0	pF
Thermal resistance	R _{θJA}			400	K/W

RATINGS AND CHARACTERISTIC CURVES LL29

Figure 1. forward current versus forward voltage (typical values)

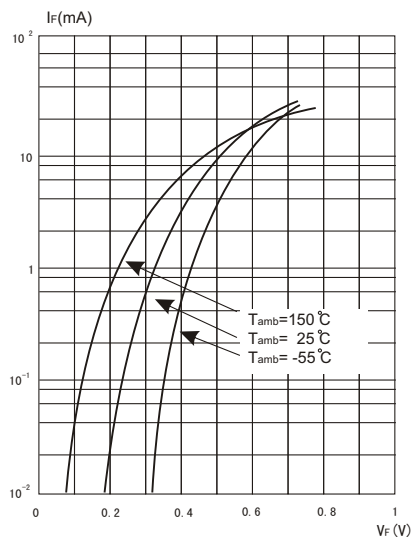


Figure 2. Capacitance C_J versus reverse applied voltage V_R (typical values)

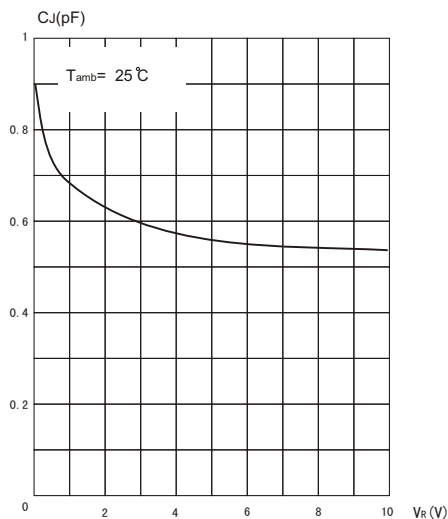


Figure 3. Reverse current versus ambient temperature

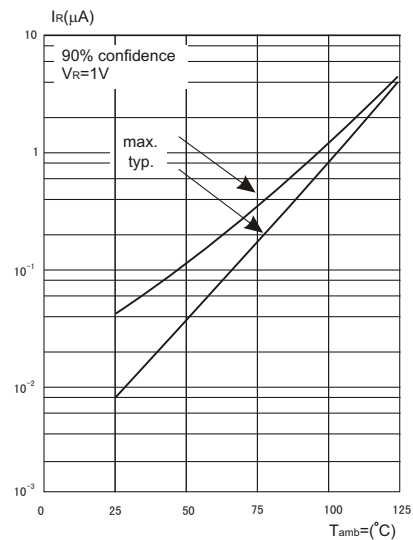


Figure 4. Reverse current versus continuous Reverse voltage (typical values)

